

Silicon NPN Power Transistors

2N5264

DESCRIPTION

- With TO-3 package
- High speed switching
- High reliability

APPLICATIONS

- Switching regulators
- DC-DC convertor
- Solid state relay
- General purpose power amplifiers

PINNING (See Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

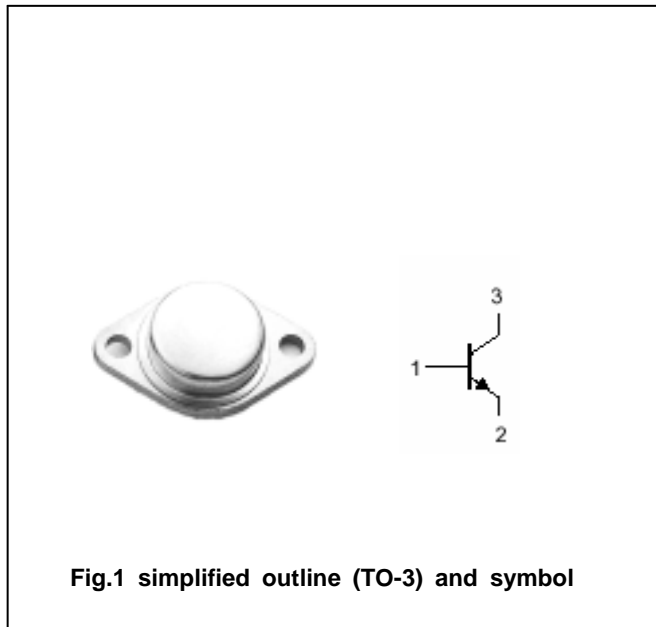


Fig.1 simplified outline (TO-3) and symbol

MAXIMUM RATINGS(Ta=25 )

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V <sub>CBO</sub>	Collector-base voltage	Open emitter	300	V
V <sub>CEO</sub>	Collector-emitter voltage	Open base	180	V
V <sub>EBO</sub>	Emitter-base voltage	Open collector	7	V
I <sub>C</sub>	Collector current		7	A
I <sub>B</sub>	Base current		2	A
P <sub>T</sub>	Total power dissipation	T <sub>c</sub> =25	87	W
T <sub>j</sub>	Junction temperature		165	
T <sub>stg</sub>	Storage temperature		-65~200	

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R <sub>th j-c</sub>	Thermal resistance from junction to case	1.0	/W

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## CHARACTERISTICS

T<sub>j</sub>=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CEQ(SUS)</sub>	Collector-emitter sustaining voltage	I <sub>C</sub> =0.1A ; I <sub>B</sub> =0	180			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =7A; I <sub>B</sub> =1.4A			1.5	V
V <sub>BEsat</sub>	Base-emitter saturation voltage	I <sub>C</sub> =7A; I <sub>B</sub> =1.4A			1.2	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =300V; I <sub>E</sub> =0			1	mA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =7V; I <sub>C</sub> =0			0.1	mA
h <sub>FE</sub>	DC current gain	I <sub>C</sub> =1A ; V <sub>CE</sub> =5V	30		300	
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =1A ; V <sub>CE</sub> =10V	50			MHz

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PACKAGE OUTLINE

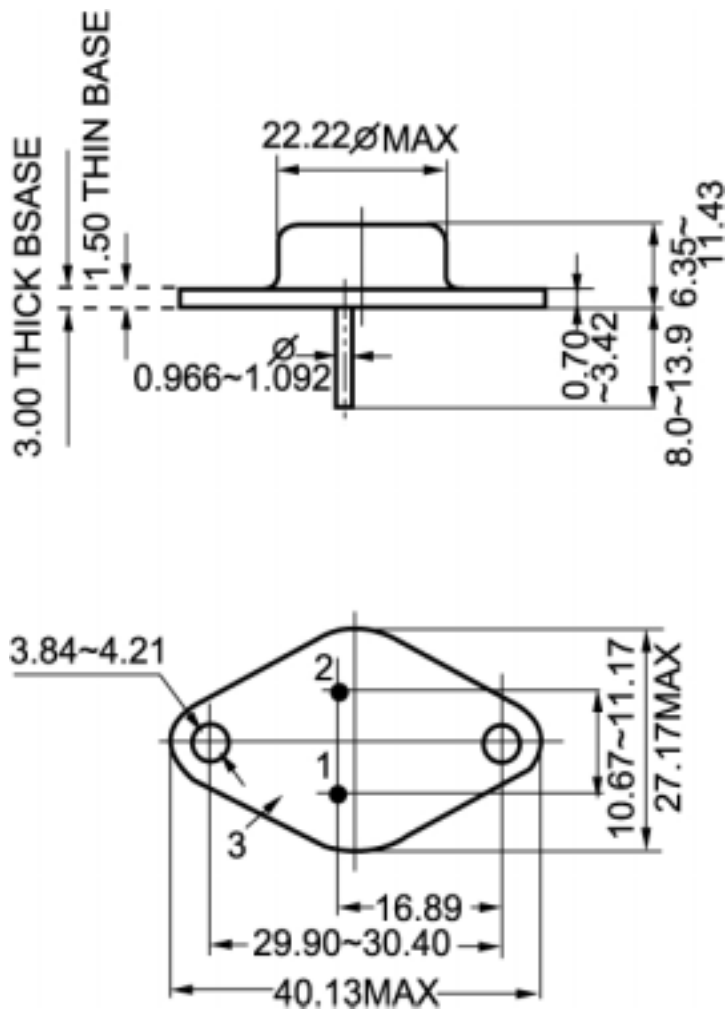


Fig.2 Outline dimensions